

TSM3404

30V N-Channel MOSFET



SOT-23

Pin Definition:



1. Gate 2. Source 3. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
30	30 @ V _{GS} = 10V	5.8	
	43 @ V _{GS} = 4.5V	5.0	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

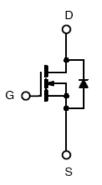
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM3404CX RF	SOT-23	3Kpcs / 7" Reel

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current		I _D	5.8	А	
Pulsed Drain Current		I _{DM}	20	Α	
Continuous Source Current (Diode Co	nduction) ^{a,b}	I _S	2.5	А	
Manipular Davida Dispiration	Ta = 25°C		0.75	\A/	
Maximum Power Dissipation P_D $Ta = 75^{\circ}C$	P_{D}	0.48	W		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Foot Thermal Resistance	R⊖ _{JF}	75	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	R⊖ _{JA}	140	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.



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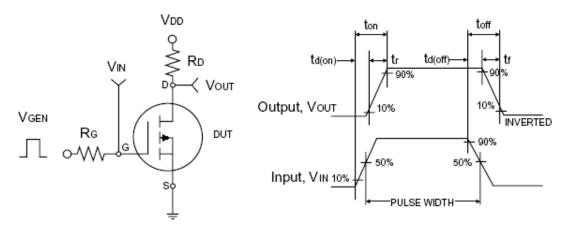


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30		1	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.4	3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	μA
Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$	I _{DSS}			1.0	μA
On-State Drain Current	$V_{DS} = 5V$, $V_{GS} = 4.5V$	I _{D(ON)}	20			Α
Proin Course On State Resistance	$V_{GS} = 10V, I_D = 5.8A$			23	30	
rain-Source On-State Resistance $V_{GS} = 4.5V, I_D = 5A$ $R_{DS(ON)}$		35	43	mΩ		
Forward Transconductance	$V_{DS} = 5V, I_{D} = 5A$	g _{fs}		25		S
Diode Forward Voltage	I _S = 1.0A, V _{GS} = 0V	V_{SD}		0.76	1	V
Dynamic ^b						
Total Gate Charge	- \/ - 15\/ - 5 0 \	Q_g		4.52		
Gate-Source Charge	V _{DS} = 15V, I _D = 5.8A, V _{GS} = 10V	Q_gs		1.24		nC
Gate-Drain Charge	V _{GS} = 10V	Q_{gd}		1.68		
Input Capacitance	\/ - 45\/ \/ - 0\/	C _{iss}		400.96	-	
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$ $V_{DS} = 1.0MHz$	C _{oss}		100.47	I	pF
Reverse Transfer Capacitance		C _{rss}		71.82		
Switching ^c						
Turn-On Delay Time	15 / D 000	t _{d(on)}		7.42		
Turn-On Rise Time	$V_{DD} = 15V, R_L = 2.2\Omega,$	t _r		3.41		nS
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 10V,$ $R_G = 6\Omega$	t _{d(off)}		20.4		113
Turn-Off Fall Time	NG - 077	t _f		3.01		

Notes:

- a. pulse test: PW $\leq 300 \mu S$, duty cycle $\leq 2\%$ b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

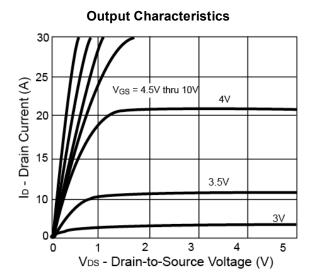




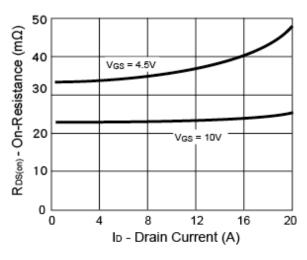




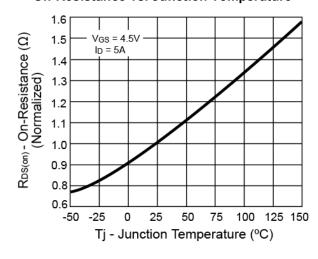
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



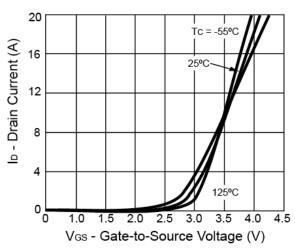
On-Resistance vs. Drain Current



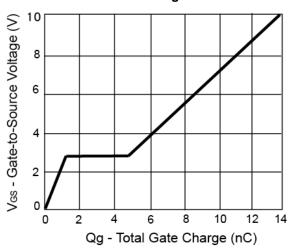
On-Resistance vs. Junction Temperature



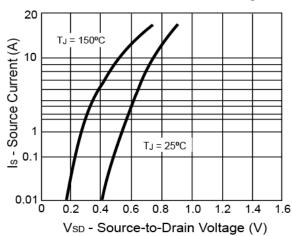
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage





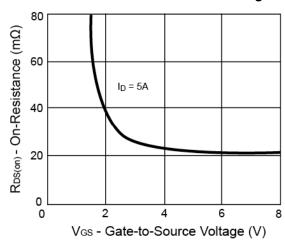


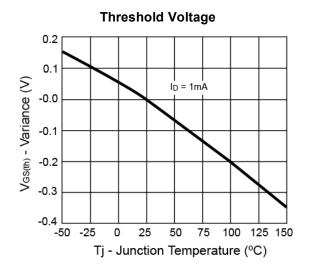




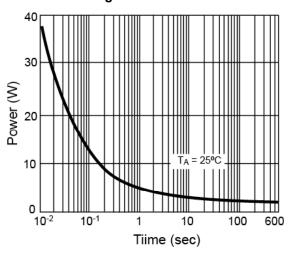
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

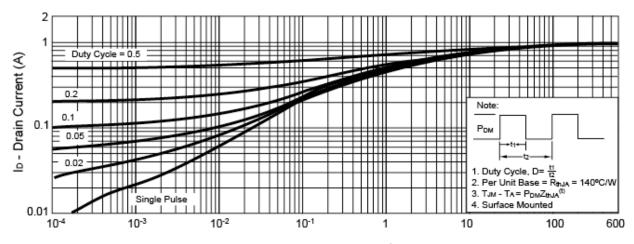




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



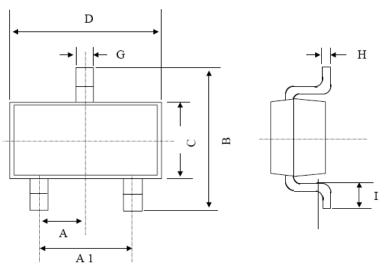
Square Wave Pulse Duration (sec)



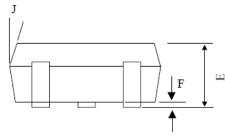




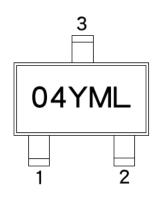
SOT-23 Mechanical Drawing



	SOT-23 DIMENSION				
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	0.95	0.95 BSC		BSC	
A1	1.9 I	BSC	0.074 BSC		
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
E	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Н	0.10	0.20	0.004	0.008	
Ī	0.30	0.60	0.012	0.024	
J	5°	10°	5°	10°	



Marking Diagram



04 = Device Code

Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



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